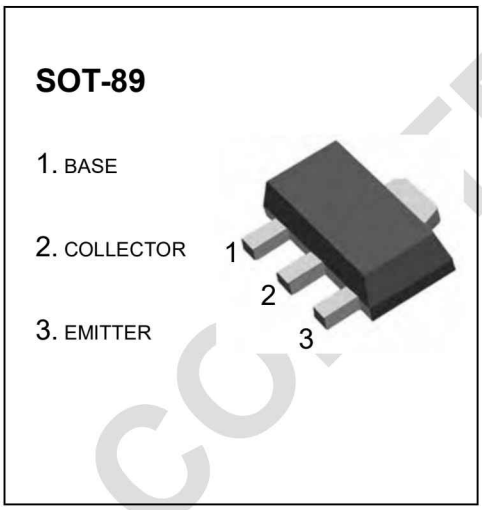
2SC2881 TRANSISTOR (NPN)



FEATURES

Power dissipation

P_{CM}: 500 mW (Tamb=25℃)

Collector current

I_{CM}: 800 mA

Collector-base voltage

$V_{(BR)CBO}$: 120 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=1mA, I_E=0	120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=10mA, I_B=0	120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=1mA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=120V, I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V, I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=5V, I_C=100mA	80		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=500mA, I_B=50mA			1	V
Base-emitter voltage	V_{BE}	V_{CE}=5V, I_C=500mA			1	V
Transition frequency	f_T	V_{CE}=5V, I_C=100mA		120		MHz
Collector output capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz			30	pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	**O**	**Y**
Range	80-160	120-240
Marking	**CO1**	**CY1**

WEJ ELECTRONIC CO.,LTD